

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	0	rekhi near sanjay.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L2	0	cherukupalli near nagendra.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L3	9	keswick near paul.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L4	631	257/356.ccls.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
5	BRS	L5	114	4 and (first near transistor)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
6	BRS	L6	4	4 and (first near transistor) near25 (charge\$1)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
7	BRS	L7	3308	(first near transistor) near25 (charge\$1)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
8	BRS	L8	0	(first near transistor) near15 (metal near wire\$1) near25 (charge\$1)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
9	BRS	L9	5	(first near transistor) near15 (wire\$1) near25 (charge\$1)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
10	BRS	L10	412	(transistor) near15 (wire\$1) near25 (charge\$1)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
11	BRS	L11	0	(transistor) near15 (wire\$1) near25 (charge\$1 near3 buildup)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
12	BRS	L12	0	(transistor) near15 (wire\$1) near25 (charge\$1 near3 build-up)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
13	BRS	L13	1	(transistor) near15 (wire\$1) near25 (build-up)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
14	BRS	L14	3	(transistor) near15 (wire\$1) near25 (build near up)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
15	BRS	L15	0	(transistor) near15 (wire\$1) near25 (buildup)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
16	BRS	L16	0	(second near transistor) near15 (wire\$1) near25 (charge41)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
17	BRS	L17	4	(second near transistor) near15 (wire\$1) near25 (charge\$1)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
18	BRS	L18	398	(second near transistor) near15 (wire\$1)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
19	BRS	L19	11	(second near transistor) near15 (metal near wire\$1)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
20	BRS	L20	73938	(transistor) near15 (metal or wire\$1)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
21	BRS	L21	8	20 and (switch\$3 near5 on)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
22	BRS	L22	11	((transistor) near15 (metal or wire\$1)) near25 (on)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
23	BRS	L23	11	((transistor) near15 (metal or wire\$1)) near15 (on)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
24	BRS	L24	71026	((transistor) near15 (charge\$1))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
25	BRS	L25	25	((transistor) near15 (charge\$1)) near10 (on)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
26	BRS	L26	33	24 and (switch\$3 near5 on)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
27	BRS	L27	725	(switch\$3 near on)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
28	BRS	L28	59	((switch\$3 near on)) near15 (transistor)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
29	BRS	L29	390	((on)) near15 (transistor)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
30	BRS	L30	18	((on)) near15 (transistor near15 discharg\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
31	BRS	L31	19	((on)) near15 (transistor near25 discharg\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
32	BRS	L32	11036	((off)) near15 (transistor near25 discharg\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
33	BRS	L33	330	((off)) near15 (second near transistor) near25 (discharg\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
34	BRS	L34	4	((off)) near15 (second near transistor) near25 (metal or wire\$1) near25 (discharg\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
35	BRS	L35	21	(second near transistor) near25 (metal or wire\$1) near25 (discharg\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
36	BRS	L36	238	((transistor) near25 (metal or wire\$1) near25 (discharg\$3)) near15 (protect\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
37	BRS	L37	14	((transistor) near25 (metal or wire\$1) near25 (discharg\$3)) near15 (protect\$3 near5 gate)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
38	BRS	L38	61	36 and charge	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
39	BRS	L39	69	36 and (coupl\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
40	BRS	L40	12	((coupl\$3 near15 transistor) near25 (metal or wire\$1) near25 (discharg\$3)) near15 (protect\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
41	BRS	L41	20513	(transistor near15 float\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
42	BRS	L42	1080	(transistor near15 float\$3) near15 (metal\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
43	BRS	L43	9	(discharg\$3) near10 (transistor near15 float\$3) near15 (metal\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
44	BRS	L44	425	(discharg\$3) near10 (transistor) near15 (metal\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
45	BRS	L45	127	(discharg\$3) near10 (transistor) near15 (protect\$3 near10 metal\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	U	1	Document ID	Title
1			US 6545915 B2	Method for driving nonvolatile semiconductor memory device
2			US 5528547 A	Electrically erasable programmable read-only memory with electric field decreasing controller
3			US 5402373 A	Electrically erasable programmable read-only memory with electric field decreasing controller
4			US 5293337 A	Electrically erasable programmable read-only memory with electric field decreasing controller
5			US 4665503 A	Non-volatile memory devices
6			US 4375087 A	Electrically erasable programmable read only memory
7			JP 08250609 A	SEMICONDUCTOR STORAGE DEVICE AND USAGE THEREOF

	U	1	Document ID	Title
8	X		US 20030007389 A	Nonvolatile semiconductor memory device drive method e.g. for rewritable flash memory, involves setting MOS transistor between local and main bit lines to half-conducting state and applying preset voltage to control gate
9	X		EP 1158535 A	Semiconductor memory device for computer system, detects memory cells which are over erased by collective erasing and writes data to over erased memory cells